

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI ASAT10** is Designed for

FEATURES:

- Input Matching Network
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	2.3 A
V_{CB0}	45 V
V_{CEO}	15 V
V_{EBO}	3.5 V
P_{DISS}	29 W @ T _C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	6.0 °C/W

PACKAGE STYLE .250 2L FLG(A)

DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.055 / 1.40	.065 / 1.65
B	.124 / 3.15	
C	.243 / 6.17	.253 / 6.43
D	.635 / 16.13	.665 / 16.89
E	.555 / 14.10	.565 / 14.35
F	.739 / 18.77	.749 / 19.02
G	.315 / 8.00	.325 / 8.26
H	.002 / 0.05	.006 / 0.15
I	.055 / 1.40	.065 / 1.65
J	.075 / 1.91	.095 / 2.41
K		.190 / 4.83
L	.245 / 6.22	.255 / 6.48
M	.092 / 2.34	

ORDER CODE: ASI10517

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CB0}	I _C = 3.0 mA	45			V
BV_{CEO}	I _C = 3.0 mA	12			V
BV_{EBO}	I _E = 3.0 mA	3.5			V
h_{FE}	V _{CE} = 5.0 V I _C = 600 mA	15		150	---
C_{OB}	V _{CB} = 28 V f = 1.0 MHz			7.0	pF
P_G η_C	V _{CC} = 28 V P _{OUT} = 10 W f = 1.65 GHz	11 45			dB %